MSKSEMI 美森科













ESD

TV

TSS

MOV

GDT

PIFD

MMBTA44-MS

Product specification





TRANSISTOR ((NPN)

FEATURES

- High Collector-Emitter Voltage
- Complement to MMBTA94-MS

Reference News

PACKAGE OUTLINE		MARKING
1 2 3	1. BASE 2. EMITTER 3.COLLECTOR	3D
SOT-23		

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	400	V
Vceo	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	6	V
lc	Collector Current-Continuous	200	mA
Ісм	Collector Current -Pulsed	300	mA
Pc	Collector Power Dissipation	350	mW
Roja	Thermal Resistance From Junction To Ambient	357	°C/W
Tj	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 ~ +150	°C

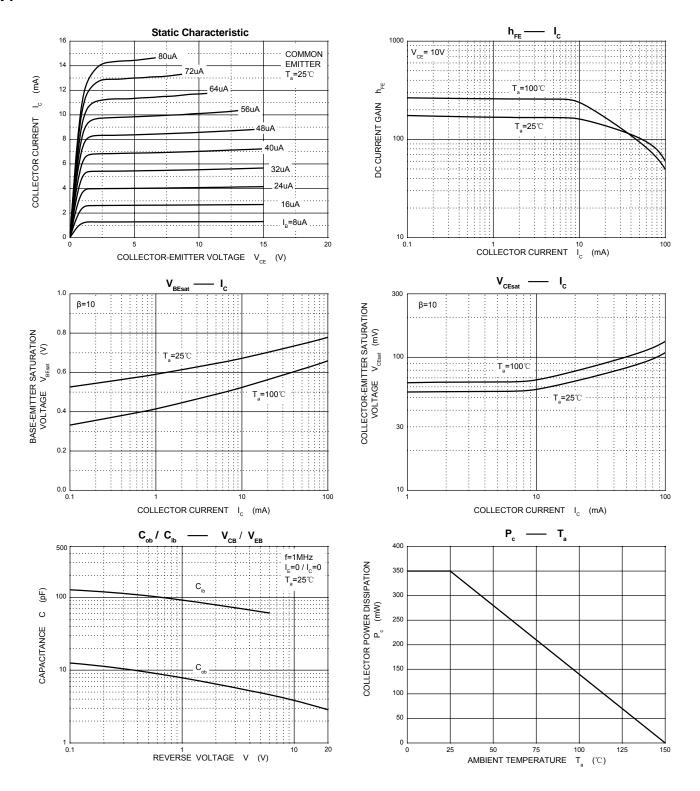
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	l _C =100μA, I _E =0	400			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	lc=1mA, l _B =0	400			V
Emitter-base breakdown voltage	V _{(BR)EBO}	l _E =10μA, I _C =0	6			V
Collector cut-off current	Ісво	V _{CB} =400V, I _E =0			0.1	μA
Emitter cut-off current	ІЕВО	V _{EB} =4V, I _C =0			0.1	μA
	h _{FE(1)} *	V _{CE} =10V, I _C =1mA	40			
DC surrent asia	h _{FE(2)} *	V _{CE} =10V, I _C =10mA	50		200	
DC current gain	h _{FE(3)} *	V _{CE} =10V, I _C =50mA	45			
	h _{FE(4)} *	V _{CE} =10V, I _C =100mA	40			
Collector-emitter saturation voltage	V _{CE(sat)1} *	lc=1mA, l _B =0.1mA			0.4	V
	V _{CE(sat)2} *	I _C =10mA, I _B =1mA			0.5	V
	V _{CE(sat)3} *	I _C =50mA, I _B =5mA			0.75	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =10mA, I _B =1mA			0.75	V
Collector output capacitance	C _{ob}	V _{CB} =20V, I _E =0, f=1MHz			7	pF
Emitter input capacitance	C _{ib}	V _{EB} =0.5V, I _C =0, f=1MHz			130	pF

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.

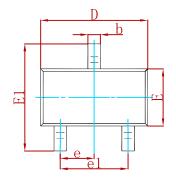


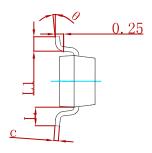
Typical Characteristics

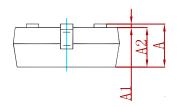




PACKAGE MECHANICAL DATA

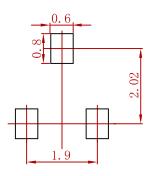






Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022	REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMBTA44-MS	SOT-23	3000



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